Amendments to the Specification:

Please amend the Title on page 1 as follows:

SEMICONDUCTOR DEVICE INCLUDES GATE INSULATING FILM HAVING A HIGH DIELECTRIC CONSTANT

Please replace the paragraph beginning at page 1, lines 5-10, with the following amended paragraph:

This application is based upon and claims the benefit of priority from the prior Japanese Patent Applications No. 3001-092531, filed March 28, 2001; and No. 2002-083380, filed March 25, 2002, and from U.S. Application No. 10/106,345, filed March 27, 2002, the entire contents of ~~both of~~ which are incorporated herein by reference.

Please replace the paragraph beginning at page 17, line 9, with the following amended paragraph:

In the MOSFET of FIG. 2, manufactured by the second embodiment ~~deseried~~ described with reference to FIGS. 5 to 10, the lines of electric force become dense at the center part of the gate insulating film 5a and sparse at the edges of the film 5a in the channel length direction when the gate voltage is applied between the gate electrode 6a and the source/drain regions 7a and 7b. Hence, the electric field is distributed to be intense at the center part of the gate insulating film 5a. The electric field can therefore be prevented from concentrating at the edges of the gate electrode 6a.